

70mA 70V(0.23mm)

**Chip Information**

Chip Size	0.23 x 0.23mm
Pad Size	0.13 x 0.13mm
Chip Quantity	209532 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

**MAXIMUM RATINGS**

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	70	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	70	V	
Average Forward Rectified Current	IF(AV)	70	mA	
Peak Forward Surge Current	IFSM	0.1	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

**ELECTRICAL CHARACTERISTICS**

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.410	0.400	0.378	V	IF=1mA Ta=25degC
	VF2	0.750	0.740	0.695	V	IF=10mA Ta=25degC
	VF3	1.000	0.900	0.820	V	IF=15mA Ta=25degC
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	0.1	0.04	0.009	uA	VR=50V Ta=25degC
	IR2	5	2	0.015	uA	VR=70V Ta=25degC
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	70	74	90	V	IR=10uA
Junction Capacitance	Cj	2			pF	V=0V,f=1MHz
Reverse Recovery Time	trr	5			nS	IF=IR=10mA irr=0.1IR

**Ordering Information**

Chip Type	Chip Thickness	Back Metal
XQA015	180 +/- 20um	Au(For Eutectic)
XQA017	150 +/- 20um	Au(For Eutectic)
XQA019	100 +/- 15um	Au(For Eutectic)

Note:  
Designed For BAS70